

N-Channel Enhancement-Mode MOSFETs

Mechanical Data

- Case: SOT-23 Molded plastic
- Epoxy: UL94V-O rate flame retardant
- RoHS compliant package

Packing & Order Information

3,000/Reel





Graphic symbol











Symbol	MILLIMETERS			
	MIN	MAX		
Α	0.8	1.2		
A1	0	0.1		
A2	0.7	1.1		
b	0.3	0.5		
С	0.1	0.2		
D	2.7	3.1		
E	2.6	3		
E1	1.4	1.8		
е	0.95 BSC			
e1	1.9 BSC			
Le	0.3	0.6		
θ1	7° NOM			



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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum Ratings (Tc=25°C unless otherwise noted)						
Parameter	Symbol	BW3402	Unit			
Drain-Source Voltage	BVDSS	30	V			
Gate- Source Voltage	VGS	12	V			
Drain Current (continuous)	ID	4.6	А			
Drain Current (pulsed)	IDM	16	А			
Thermal resistance, junction to ambient air	PD	1380	mW			
Junction	TJ	150	°C			
Storage Temperature	TSTG	-55 to +150	°C			

Maximum Ratings (Tc=25°C unless otherwise noted)					
Parameter	Symbol	Min	Тур.	Max.	Units
Drain-Source Breakdown Voltage ($I_D = 250uA, V_{GS} = 0 V$)	BV_{DSS}	30			V
Gate Threshold Voltage ($I_D = 250 \text{uA}, V_{GS} = V_{DS}$)	VGS(th)	0.7		18	V
Diode Forward Voltage Drop ($I_S = 1 \text{ A}, V_{GS} = 0 \text{ V}$)	VSD			1	V
Zero Gate Voltage Drain Current					
(VGS=0V, VDS= 24V)	IDSS			1	uA
(VGS=0V, VDS= 24V, TA=55°C)				5	

Maximum Ratings (Tc=25°C unless otherwise noted)					
Parameter	Symbol	Min	Тур.	Max.	Units
Gate Body Leakage (V_{GS} =+12 V, V_{DS} = 0 V)	IGSS			+/-100	nA
Static Drain-Source On-State Resistance				30	mΩ
$(I_D = 4.6 \text{ A}, V_{GS} = 10 \text{ V})$					
Static Drain-Source On-State Resistance				50	mΩ
$(I_D = 4 A, V_{GS} = 4.5 V)$					
Static Drain-Source On-State Resistance				100	۳E
$(I_{D} = 1 \text{ A}, V_{GS} = 2.5 \text{ V})$				100	рг
Input Capacitance ($V_{GS} = 0 V$, $V_{DS} = 15 V$, f = 1MHz)	CISS		954		pF
Output Capacitance ($V_{GS} = 0 V$, $V_{DS} = 15 V$, f = 1MHz)	COSS		115		pF
Turn-ON Time (V_{DS} = 15 V, V_{GS} = 10 V, R_{GEN} = 6 \Omega)	t(on)		6.3		ns
Turn-OFF Time (V_{DS} = 15 V, V_{GS} = 10 V, R_{GEN} = 6 \Omega)	t(off)		38.2		ns

Pulse Width<300µs; Duty Cycle<2.0%



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Characteristics Curve





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Characteristics Curves





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